

/ Descriptions

TO-252 N MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

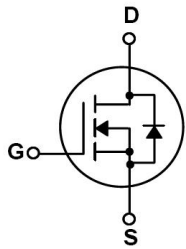
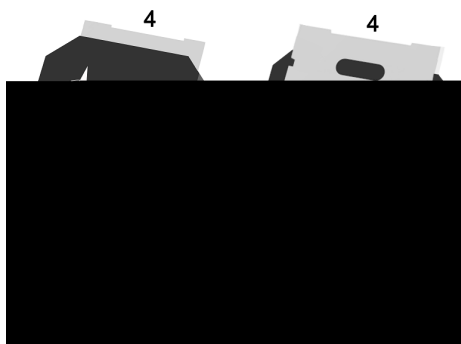
/ Features $V_{DS}=500V$ $I_D=3A$ $R_{DS(ON)}@10V \leq 3.5$ (Typ. 2.2)

Fast Switching.

HF Product.

/ Applications

These devices are well suited for power switch circuit of adaptor and charger, intergrate fast recovery diode.

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

BRD3N50F

Rev.A Apr.-2024

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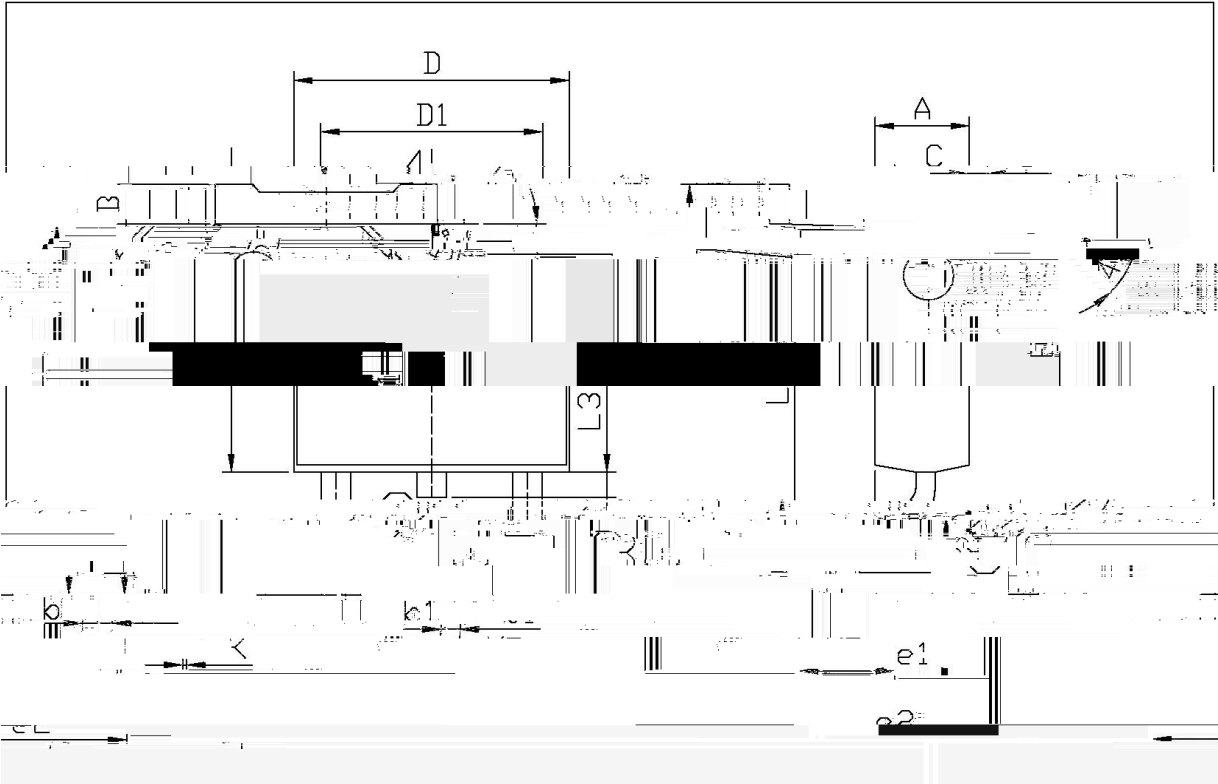
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	500	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	3	A
Drain Current - Pulsed	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	115.6	mJ
Avalanche Current	I_{AS}	5.1	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	45	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Junction to Ambient	$R_{\theta JA}$	100	/W
Junction to Case	$R_{\theta JC}$	2.78	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\text{ A}$	500			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}				

Parameter



/ Package Dimensions

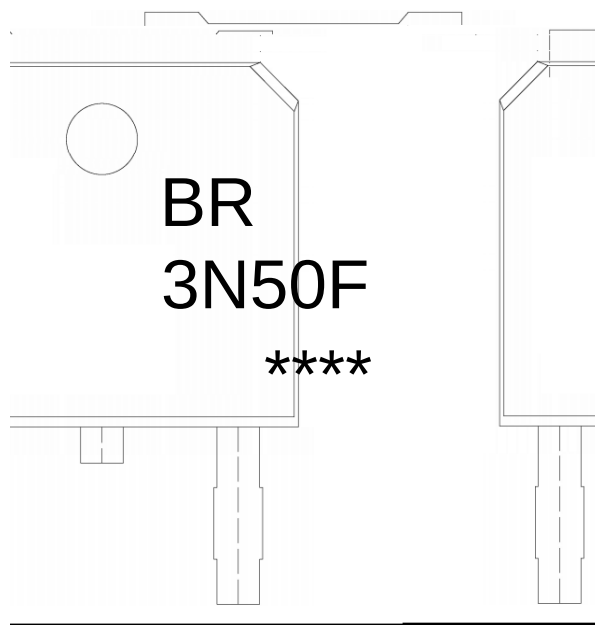


单位: mm

Dimensions, Millimeters		Dimensions, Millimeters	
Min	Max	Min	Max
1.25	1.25	2.24	2.34
0.00	0.00	4.43	4.73
5.5	5.5	9.85	10.35
0.00	0.00	0.45	0.55
0.00	0.00	6.45	6.75
0.00	0.00	5.10	5.50
0.00	0.00	0.00	0.00

T0-252

/ Marking Instructions



BR

3N50F

Note:

BR: Company Code

3N50F: Product Type Code

****: Lot No. Code, code change with Lot No

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